

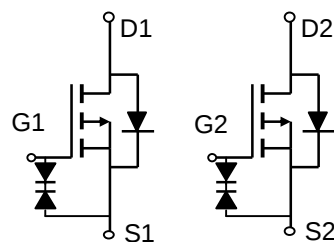
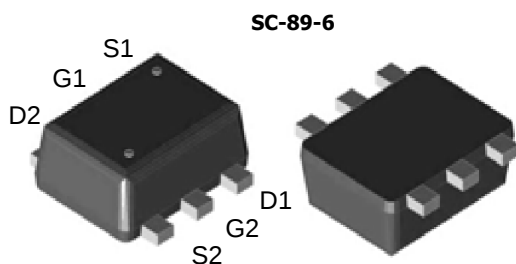
AO5803E
Dual P-Channel Enhancement Mode Field Effect Transistor
General Description

The AO5803E/L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge, and operation with gate voltages as low as 1.8V, in the small SC89-6L footprint. It can be used as load switching, and wide variety of FET applications. AO5803E and AO5803EL are electrically identical.

- RoHS compliant
- AO5803EL is Halogen Free

Features

- V_{DS} (V) = -20V
- I_D = -0.6A (V_{GS} = -4.5V)
- $R_{DS(ON)} < 0.8\Omega$ (V_{GS} = -4.5V)
- $R_{DS(ON)} < 1.0\Omega$ (V_{GS} = -2.5V)
- $R_{DS(ON)} < 1.25\Omega$ (V_{GS} = -1.8V)

ESD PROTECTED

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current ^{A, F}	I_D	-0.6	A
$T_A=25^\circ\text{C}$		-0.4	
Pulsed Drain Current ^B	I_{DM}	-3	
Power Dissipation ^A	P_D	0.4	W
$T_A=25^\circ\text{C}$		0.24	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	275	330	$^\circ\text{C/W}$
$t \leq 10\text{s}$				
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	360	450	$^\circ\text{C/W}$
Steady-State				
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	300	350	$^\circ\text{C/W}$
Steady-State				

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V			-1	μA
		T _J =55℃			-5	
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±4.5V			±1	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =-250μA	-0.4	-0.5	-0.9	V
I _{D(ON)}	On state drain current	V _{GS} =-4.5V, V _{DS} =-5V	-3			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V, I _D =-0.6A		0.62	0.8	Ω
		T _J =125℃		0.87	1.1	
		V _{GS} =-2.5V, I _D =-0.5A		0.79	1	Ω
		V _{GS} =-1.8V, I _D =-0.4A		0.96	1.25	Ω
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-0.6A		0.9		S
V _{SD}	Diode Forward Voltage	I _S =-0.1A,V _{GS} =0V		-0.81	-1	V
I _S	Maximum Body-Diode Continuous Current				-0.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-10V, f=1MHz		72	100	pF
C _{oss}	Output Capacitance			17		pF
C _{rss}	Reverse Transfer Capacitance			9		pF
SWITCHING PARAMETERS						
t _{D(on)}	Turn-On DelayTime	V _{GS} =-4.5V, V _{DS} =-10V, R _L =16.7Ω, R _{GEN} =3Ω		60.5		ns
t _r	Turn-On Rise Time			150		ns
t _{D(off)}	Turn-Off DelayTime			612		ns
t _f	Turn-Off Fall Time			436		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-0.6A, dI/dt=100A/μs, V _{GS} =-9V		27	35	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-0.6A, dI/dt=100A/μs, V _{GS} =-9V		8.3		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

F: The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

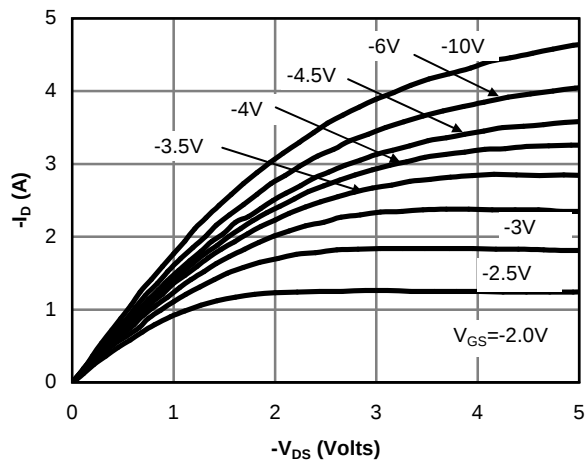


Figure 1: On-Region Characteristics

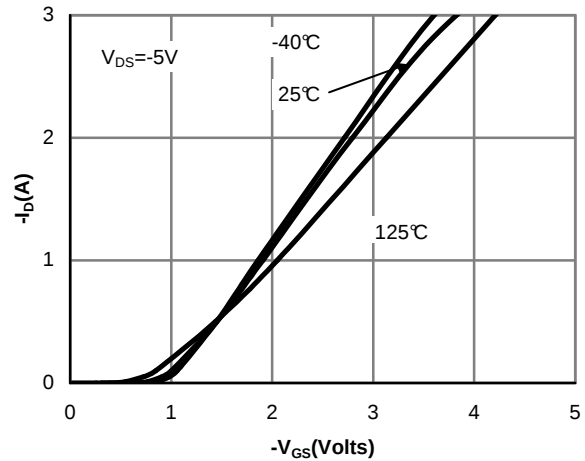


Figure 2: Transfer Characteristics

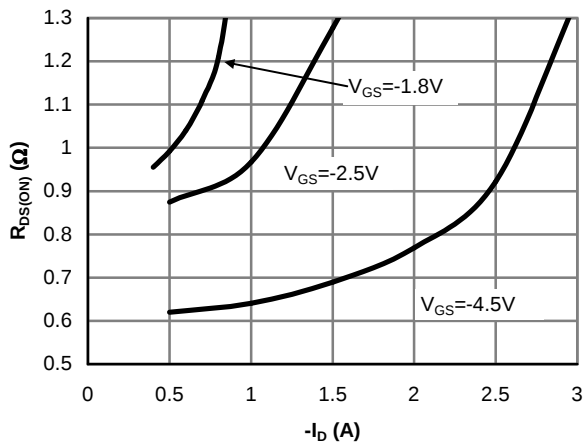


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

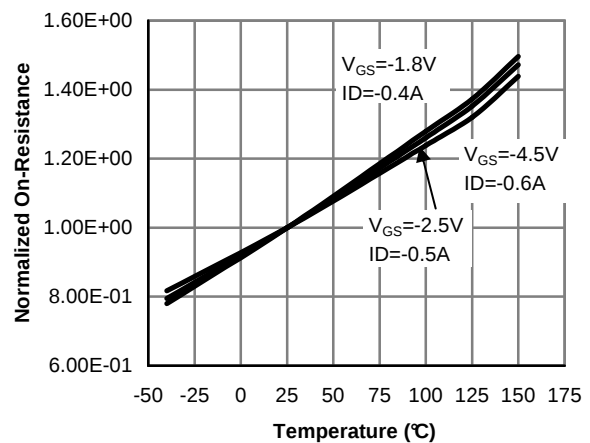


Figure 4: On-Resistance vs. Junction Temperature

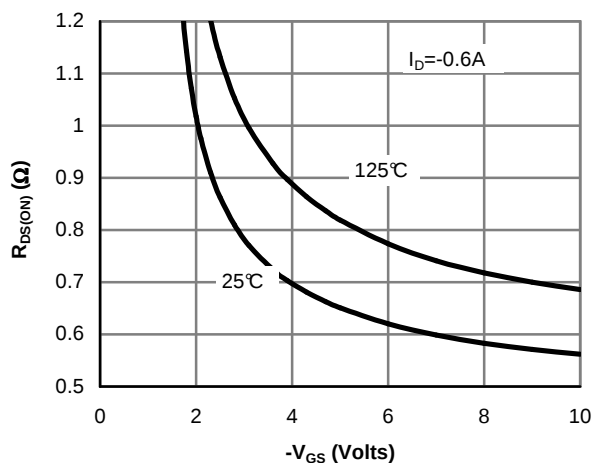


Figure 5: On-Resistance vs. Gate-Source Voltage

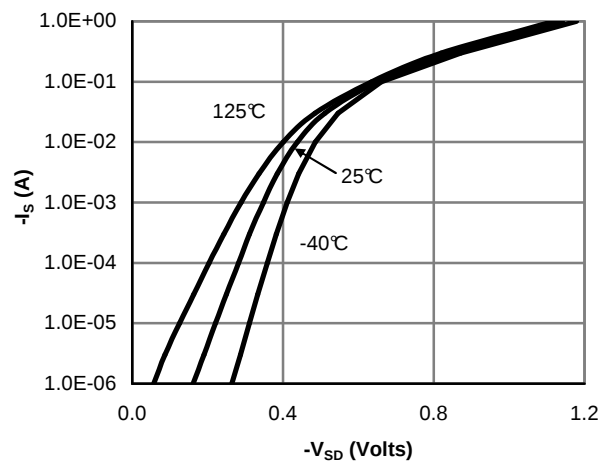


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

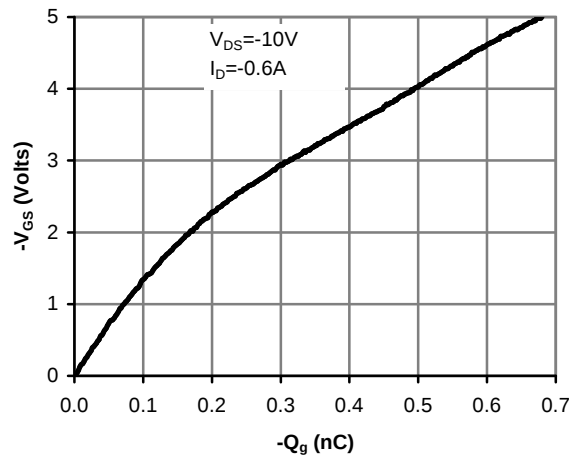


Figure 7: Gate-Charge Characteristics

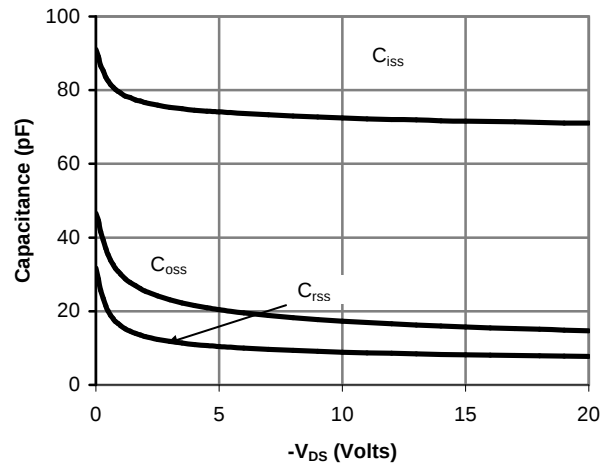


Figure 8: Capacitance Characteristics

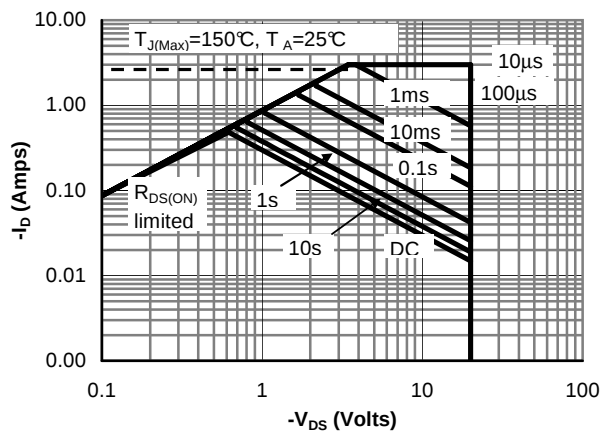


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

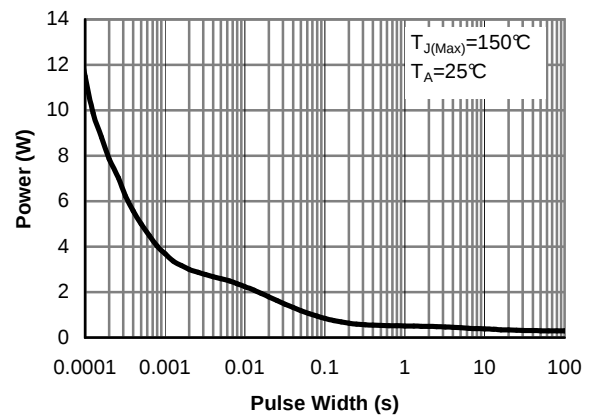


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

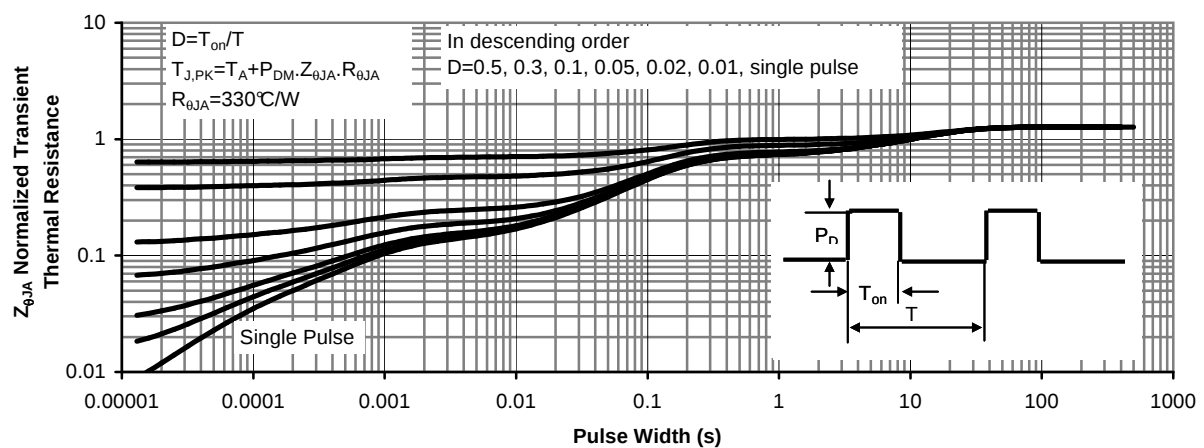
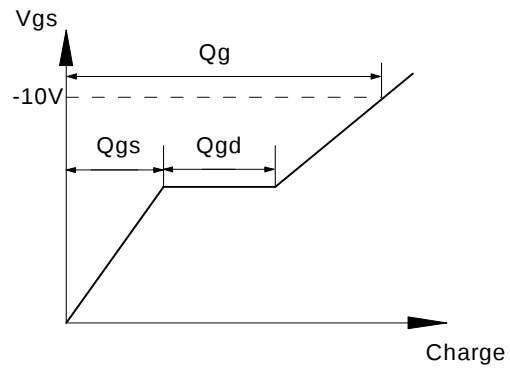
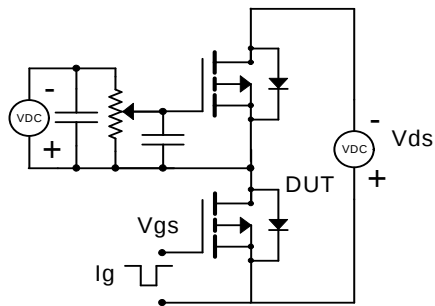
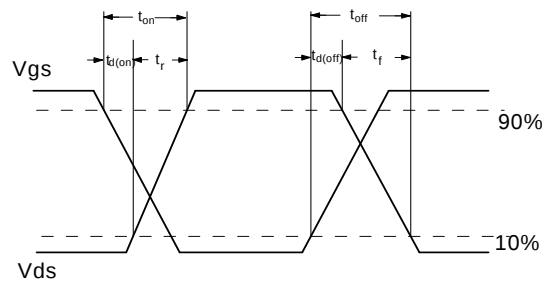
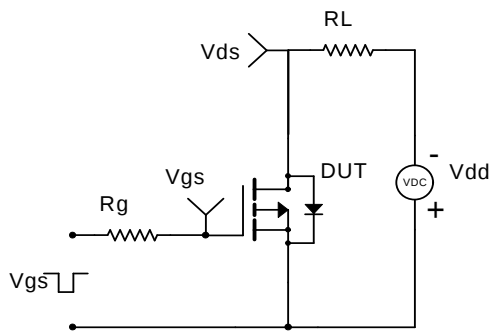


Figure 11: Normalized Maximum Transient Thermal Impedance

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

